

Dual Schmitt-Trigger Inverter

NL27WZ14

The NL27WZ14 is a high performance dual inverter with Schmitt-Trigger inputs operating from a 1.65 to 5.5 V supply.

Features

- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 3.2 ns t_{PD} at $V_{CC} = 5 \text{ V (Typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Sink 32 mA at 4.5 V
- Available in SC-88, SC-74, TSOP-6 and UDFN6 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

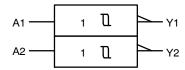
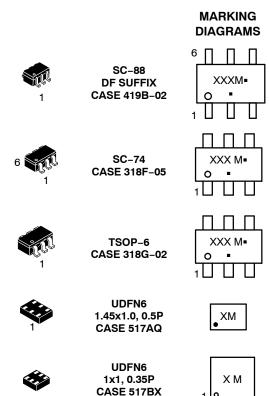


Figure 1. Logic Symbol



X, XXX = Specific Device Code M = Date Code*

■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

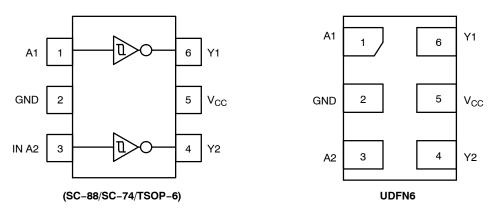


Figure 2. Pinout (Top View)

PIN ASSIGNMENT

Pin	Function
1	A1
2	GND
3	A2
4	Y2
5	V _{CC}
6	Y1

FUNCTION TABLE

A Input	Y Output
L	Н
Н	L

MAXIMUM RATINGS

Symbol	Characteristics	3	Value	Units
V _{CC}	DC Supply Voltage	TSOP-6, SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{IN}	DC Input Voltage	TSOP-6, SC-88 (NLV) SC-88, SC-74, UDFN6	-0.5 to +7.0 -0.5 to +6.5	V
V _{OUT}	DC Output Voltage TSOP-6, SC-88 (NLV)	Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode ($V_{\rm CC}$ = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +7.0 -0.5 to +7.0	V
	DC Output Voltage SC-88, SC-74, UDFN6	Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} +0.5 -0.5 to +6.5 -0.5 to +6.5	V
I _{IK}	DC Input Diode Current, V _{IN} < GND		-50	mA
I _{OK}	DC Output Diode Current, V _{OUT} < GND		-50	mA
I _{OUT}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or Ground Pin		±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
TJ	Junction Temperature under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88 SC-74 UDFN6	377 320 154	°C/W
P _D	Power Dissipation in Still Air	SC-88 SC-74 UDFN6	332 390 812	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flamebility Rating	Oxygen Index: 28 to 34	UL 94-V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model (NLV) Charged Device Model	2000 1000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Applicable to devices with outputs that may be tri–stated.

- Application to define with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Para	meter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode ($V_{CC} = 0 \text{ V}$)	0 0 0	V _{CC} 5.5 5.5	٧
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Transition Rise or Fall Rate	$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0 0 0 0	No Limit No Limit No Limit No Limit	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

				T _A	= 25°C		-40°C ≤ T _A	≤ 85°C	-55°C ≤ T _A :	≤ 125°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _T +	Positive Input		1.65	0.6	1.0	1.4	0.6	1.4	0.6	1.4	٧
	Threshold Voltage (NLV)		2.3	1.0	1.5	1.8	1.0	1.8	1.0	1.8	
	vollago (1421)		2.7	1.2	1.7	2.0	1.2	2.0	1.2	2.0	
			3.0	1.3	1.9	2.2	1.3	2.2	1.3	2.2	
			4.5	1.9	2.7	3.1	1.9	3.1	1.9	3.1	
			5.5	2.2	3.3	3.6	2.2	3.6	2.2	3.6	
	Positive Input		1.65	_	1.0	1.4	_	1.4	-	1.4	٧
	Threshold Voltage		2.3	-	1.5	1.8	-	1.8	-	1.8	
			2.7	_	1.7	2.0	_	2.0	-	2.0	
			3.0	_	1.9	2.2	_	2.2	-	2.2	
			4.5	-	2.7	3.1	-	3.1	-	3.1	
			5.5	_	3.3	3.6	_	3.6	-	3.6	
V _T -	Negative		1.65	0.2	0.5	0.8	0.2	0.8	0.2	0.8	٧
	Input Threshold		2.3	0.4	0.75	1.15	0.4	1.15	0.4	1.15	
	Voltage (NLV)		2.7	0.5	0.87	1.4	0.5	1.4	0.5	1.4	
			3.0	0.6	1.0	1.5	0.6	1.5	0.6	1.5	
			4.5	1.0	1.5	2.0	1.0	2.0	1.0	2.0	
		5.5	1.2	1.9	2.3	1.2	2.3	1.2	2.3		
	Negative		1.65	0.2	0.5	-	0.2	-	0.2	-	٧
Input Threshold Voltage		2.3	0.4	0.75	-	0.4	-	0.4	-		
			2.7	0.5	0.87	-	0.5	-	0.5	-	
			3.0	0.6	1.0	-	0.6	-	0.6	-	
			4.5	1.0	1.5	-	1.0	-	1.0	-	1
			5.5	1.2	1.9	-	1.2	-	1.2	-	
V _H	Input		1.65	0.1	0.48	0.9	0.1	0.9	0.1	0.9	٧
	Hysteresis Voltage		2.3	0.25	0.75	1.1	0.25	1.1	0.25	1.1	
			2.7	0.3	0.83	1.15	0.3	1.15	0.3	1.15	
			3.0	0.4	0.93	1.2	0.4	1.2	0.4	1.2	
			4.5	0.6	1.2	1.5	0.6	1.5	0.6	1.5	
			5.5	0.7	1.4	1.7	0.7	1.7	0.7	1.7	
V _{OH}	High-Level	$I_{OH} = -100 \mu A$	1.65 to 5.5	V _{CC} - 0.1	V_{CC}	-	V _{CC} - 0.1	-	V _{CC} - 0.1	-	٧
	Output Voltage	$I_{OH} = -4 \text{ mA}$	1.65	1.29	1.52	-	1.29	-	1.29	-	
	$V_{IN} = V_{IH}$ or	$I_{OH} = -8 \text{ mA}$	2.3	1.9	2.1	-	1.9	_	1.9	-	
	V _{IL}	I _{OH} = -12 mA	2.7	2.2	2.4	-	2.2	-	2.2	-	
		$I_{OH} = -16 \text{ mA}$	3.0	2.4	2.7	-	2.4	-	2.4	-	
		$I_{OH} = -24 \text{ mA}$	3.0	2.3	2.5	-	2.3	-	2.3	-	
		$I_{OH} = -32 \text{ mA}$	4.5	3.8	4	-	3.8	-	3.8	-	
V _{OL}	Low-Level	I _{OL} = 100 μA	1.65 to 5.5	-	-	0.1	-	0.1	-	0.1	٧
	Output Voltage	I _{OL} = 4 mA	1.65	_	0.08	0.24	_	0.24	-	0.24	
	$V_{IN} = V_{IH}$ or	I _{OL} = 8 mA	2.3	-	0.2	0.3	-	0.3	-	0.3	
	V _{IL}	I _{OL} = 12 mA	2.7	_	0.22	0.4	_	0.4	-	0.4	
		-	0.28	0.4	-	0.4	-	0.4			
		I _{OL} = 24 mA	3.0	-	0.38	0.55	-	0.55	-	0.55	
		I _{OL} = 32 mA	4.5	-	0.42	0.55	-	0.55	_	0.55	

DC ELECTRICAL CHARACTERISTICS

				TA	= 25°C		-40°C ≤ T _A	≤ 85°C	-55°C ≤ T _A ≤	≤ 125°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	ı	-	±0.1	-	±1.0	ı	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0	-	-	1	-	10	-	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V or GND	5.5	I	-	1	-	10	-	10	μΑ

AC ELECTRICAL CHARACTERISTICS

				1	A = 25°C		-40°C ≤ 7	Γ _A ≤ 85°C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
tPLH, Propagation Delay, A to Y	$RL = 1 M\Omega$, CL = 15 pF	1.65 to 1.95	-	7.1	13	-	14.5	-	15.5	ns	
	(i igules 3 aliu 4)	igures 3 and 4) RL = 1 M Ω ,	2.3 to 2.7	-	4.3	7.4	-	8.1	-	9.1	
	CL = 15 pF	3.0 to 3.6	-	3.3	5	-	5.5	-	6.5		
			4.5 to 5.5	_	2.7	4.1	-	4.5	-	5.5	
	RL = 500 Ω , 3.0 to 3.6	3.0 to 3.6	-	4	6	-	6.6	=	7.6		
		CL = 50 pF	4.5 to 5.5	_	3.2	4.9	_	5.4	_	6.4	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	2.5	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.5 \text{ V}, V_I = 0 \text{ V or } V_{CC}$	4.0	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.0 V, V_{IN} = 0 V or V_{CC}	11 12.5	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in}$) I_{CC} . C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in}$) $I_{CC} \cdot V_{CC}$.

Test

t_{PLH} / t_{PHL}

t_{PLZ} / t_{PZL}

 t_{PHZ} / t_{PZH}

Switch

Position

Open 2 x V_{CC}

GND

 C_L, pF

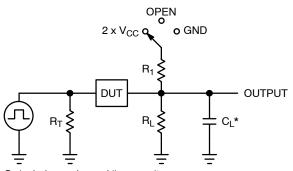
See AC Characteristics Table

See AC Characteristics Table

See AC Characteristics Table

 $\mathsf{R}_\mathsf{L}, \Omega$

 R_1, Ω



X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit

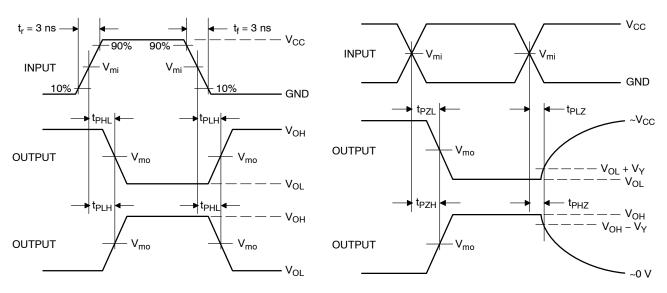


Figure 4. Switching Waveforms

		V _n		
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t _{PZL} , t _{PLZ} , t _{PZH} , t _{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} / 2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} / 2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} / 2	V _{CC} /2	0.3

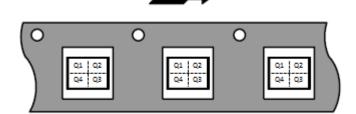
ORDERING INFORMATION

Device	Package	Specific Device Code	Pin1 Orientation (See below)	Shipping [†]
NL27WZ14DFT2G	SC-88	MA	Q4	3000 / Tape & Reel
NL27WZ14DFT2G-L22348**	SC-88	MA	Q4	3000 / Tape & Reel
NL27WZ14DFT4G	SC-88	MA	Q4	10000 / Tape & Reel
NLV27WZ14DFT2G*	SC-88	MA	Q4	3000 / Tape & Reel
NL27WZ14DTT1G**	TSOP-6	MA	Q4	3000 / Tape & Reel
NL27WZ14DBVT1G	SC-74	MA	Q4	3000 / Tape & Reel
NL27WZ14MU1TCG	UDFN6, 1.45 x 1.0, 0.5P	P (Rotated 90° CW)	Q4	3000 / Tape & Reel
NL27WZ14MU3TCG	UDFN6, 1.0 x 1.0, 0.35P	3 (Rotated 90° CW)	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel

Direction of Feed



^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

^{**}Please refer to NLV specifications for this device.





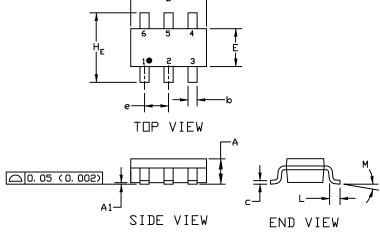
SC-74 CASE 318F **ISSUE P**

DATE 07 OCT 2021

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 1.
- CONTROLLING DIMENSION: INCHES 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.

	MI	LLIMETER	25	INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
A	0. 90	1. 00	1. 10	0. 035	0. 039	0. 043
A1	0. 01	0. 06	0. 10	0. 001	0. 002	0. 004
ھ	0, 25	0. 37	0. 50	0. 010	0. 015	0. 020
U	0.10	0. 18	0. 26	0. 004	0. 007	0. 010
D	2. 90	3. 00	3. 10	0. 114	0. 118	0. 122
E	1. 30	1. 50	1. 70	0. 051	0. 059	0. 067
e	0. 85	0. 95	1. 05	0. 034	0. 037	0. 041
Η _E	2. 50	2. 75	3. 00	0. 099	0. 108	0. 118
١	0, 20	0. 40	0. 60	0, 008	0. 016	0. 024
М	0*		10*	0*		10*



GENERIC MARKING DIAGRAM*



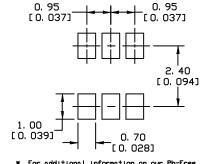
XXX = Specific Device Code

= Date Code M

= Pb-Free Package (Note: Microdot may be in either location)

device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

*This information is generic. Please refer to



For additional information on our Pb-Free strategy and soldering details, please download the DN Seniconductor Soldering and Mounting Techniques Reference Manual, SDLDERRNO.

SOLDERING FOOTPRINT

STYLE 1: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. ANODE 6. CATHODE	STYLE 2: PIN 1. NO CONNECTION 2. COLLECTOR 3. EMITTER 4. NO CONNECTION 5. COLLECTOR 6. BASE	STYLE 3: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 4: PIN 1. COLLECTOR 2 2. EMITTER 1/EMITTER 2 3. COLLECTOR 1 4. EMITTER 3 5. BASE 1/BASE 2/COLLECTOR 3 6. BASE 3	STYLE 5: PIN 1. CHANNEL 1 2. ANODE 3. CHANNEL 2 4. CHANNEL 3 5. CATHODE 6. CHANNEL 4	STYLE 6: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 7: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 8: PIN 1. EMITTER 1 2. BASE 2 3. COLLECTOR 2 4. EMITTER 2 5. BASE 1 6. COLLECTOR 1	STYLE 9: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 10: PIN 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 11: PIN 1. EMITTER 2. BASE 3. ANODE/CATHOD 4. ANODE 5. CATHODE 6. COLLECTOR	E

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DESCRIPTION:	SC-74		PAGE 1 OF 1

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TSOP-6 CASE 318G-02 **ISSUE V**

12

C SEATING PLANE

DATE 12 JUN 2012

NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
- LEAD THIORNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D
- AND E1 ARE DETERMINED AT DATUM H.
 PIN ONE INDICATOR MUST BE LOCATED IN THE INDICATED ZONE.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	0.90	1.00	1.10	
A1	0.01	0.06	0.10	
b	0.25	0.38	0.50	
С	0.10	0.18	0.26	
D	2.90	3.00	3.10	
Е	2.50	2.75	3.00	
E1	1.30	1.50	1.70	
е	0.85	0.95	1.05	
Ĺ	0.20	0.40	0.60	
L2	0.25 BSC			
М	Uo.		100	

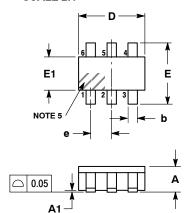
STYLE 5: PIN 1. EMITTER 2 2. BASE 2

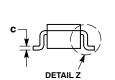
BASE 1

COLLECTOR 1 EMITTER 1

COLLECTOR 2

3.





DETAIL Z

Н

TYLE 1:	STYLE 2:
PIN 1. DRAIN	PIN 1. EMITTER 2
2. DRAIN	2. BASE 1
3. GATE	3. COLLECTOR 1
4. SOURCE	4. EMITTER 1
5. DRAIN	5. BASE 2
6. DRAIN	6. COLLECTOR 2
TYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C	

COLLECTOR

6. EMITTER

2. SOURCE 2

DRAIN 2

DRAIN 1

3. GATE 2

STYLE 13: PIN 1. GATE 1

5. SOURCE 1

S

S

3. D(in)+ 4. D(out)+ 5. D(out) 6. GND



STYLE 15: PIN 1. ANODE SOURCE 3. GATE DRAIN

STYLE 3: PIN 1. ENABLE 2. N/C

6. V out

5. V in

3. R BOOST 4. Vz

5. N/C 6. CATHODE



STYLE 16: PIN 1. ANODE/CATHODE

COLLECTOR

CATHODE

3 FMITTER

2. BASE

5. ANODE

6. LOAD	6
STYLE 10: PIN 1. D(OUT)+ 2. GND 3. D(OUT)- 4. D(IN)- 5. VBUS 6. D(IN)+	STYLE PIN 1 2 3 4 5 6

SOURCE 1 DRAIN 2 SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2

STYLE 17: PIN 1. EMITTER

2. BASE

STYLE 12: 2. GROUND 3. I/O 4. I/O 6. I/O

STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR

3. BASE 4. EMITTER

5. COLLECTOR 6. COLLECTOR

CATHODE/DRAIN **RECOMMENDED SOLDERING FOOTPRINT***

CATHODE/DRAIN

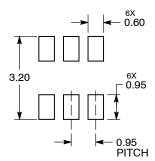
CATHODE/DRAIN

STYLE 14: PIN 1. ANODE

5.

3 GATE

SOURCE



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*

M

for actual part marking. Pb-Free indicator, "G" or microdot '

3 ANODE/CATHODE

CATHODE

COLLECTOR





XXX = Specific Device Code

= Pb-Free Package

= Date Code

XXX = Specific Device Code Α =Assembly Location

", may or may not be present.

Υ = Year

W = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet

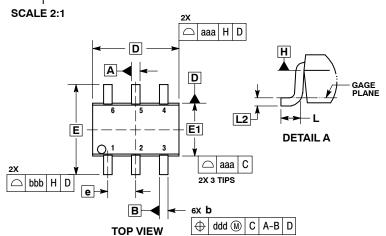
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DESCRIPTION:	TSOP-6		PAGE 1 OF 1

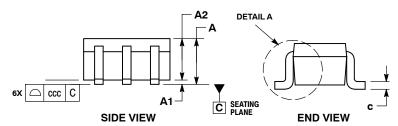
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SC-88/SC70-6/SOT-363 CASE 419B-02 **ISSUE Y**

DATE 11 DEC 2012





NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
- CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H. DATUMS A AND B ARE DETERMINED AT DATUM H. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.

- DIMENSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.000		0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
С	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
е		0.65 BS	С	0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC				0.006 BS	SC
aaa	0.15				0.006	
bbb	0.30				0.012	
ccc		0.10		0.004		
ddd		0.10			0.004	

MARKING DIAGRAM*



GENERIC

XXX = Specific Device Code

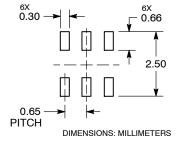
= Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)

- *Date Code orientation and/or position may vary depending upon manufacturing location.
- *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DE	SCRIPTION:	SC-88/SC70-6/SOT-363		PAGE 1 OF 2

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SC-88/SC70-6/SOT-363 CASE 419B-02 ISSUE Y

DATE 11 DEC 2012

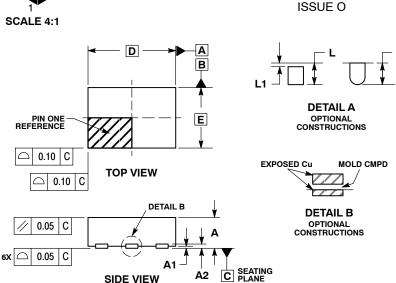
STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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6X L

6X b

0.10 | C | A | B

0.05 C NOTE 3

UDFN6, 1.45x1.0, 0.5P CASE 517AQ

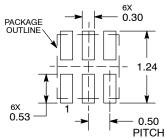


DATE 15 MAY 2008

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM THE TERMINAL TIP.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A2	0.07 REF			
b	0.20	0.30		
D	1.45 BSC			
Е	1.00 BSC			
Ф	0.50 BSC			
L	0.30	0.40		
L1		0.15		

MOUNTING FOOTPRINT



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

BOTTOM VIEW



= Specific Device Code

= Date Code

е

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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DESCRIPTION:	UDFN6, 1.45x1.0, 0.5P		PAGE 1 OF 1

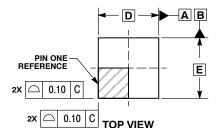
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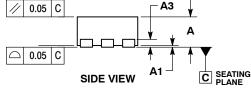


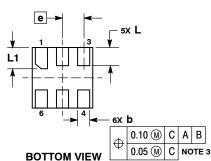


UDFN6, 1x1, 0.35P CASE 517BX **ISSUE O**

DATE 18 MAY 2011





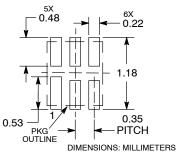


NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN
- 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.55		
A1	0.00	0.05		
A3	0.13 REF			
b	0.12	0.22		
D	1.00 BSC			
E	1.00 BSC			
е	0.35 BSC			
L	0.25	0.35		
L1	0.30	0.40		

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



X = Specific Device Code

M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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